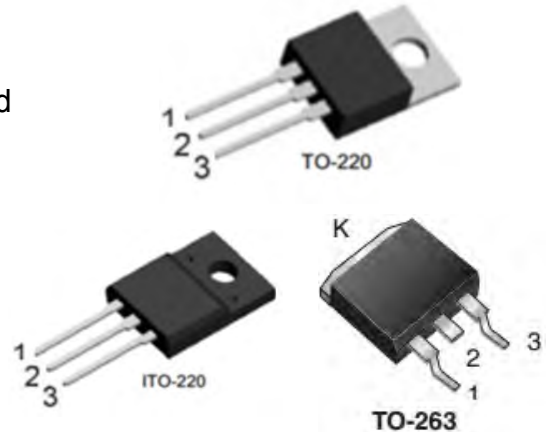
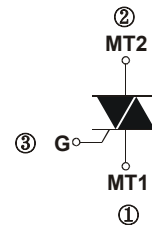


**DESCRIPTION:**

BTB16 Triacs is fabricated using separation diffusion processes, the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability, the Triacs series is suitable for domestic lighting, heating and motor speed controllers.

**MAIN FEATURES**

Symbol	Value	Unit
V_{DRM}/V_{RRM}	600 / 800	V
$I_{T(RMS)}$	16	A

Gnd Vc`**ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	$^{\circ}C$
Operating junction temperature range		T_j	-40 - 125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)		V_{DRM}	600 / 800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)		V_{RRM}	600 / 800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	$T_C=105^{\circ}C$	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, $F=50Hz$)		I_{TSM}	160	A
I^2t value for fusing ($t_p=10ms$)		I^2t	144	A^2s



**Electrical characteristics ($T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)
Snubberless and logic level (3 quadrants)**

Symbol	Test conditions	Quadrant		Value			Unit
				SW	CW	BW	
$I_{GT}^{(1)}$	$V_D = 12\text{ V}$	I - II - III	Max.	10	35	50	mA
V_{GT}	$R_L = 33\ \Omega$	I - II - III	Max.	1.3			V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_j = 125\text{ }^\circ\text{C}$	I - II - III	Min.	0.2			V
I_H	$I_T = 500\text{ mA}$		Max.	15	35	50	mA
I_L	$I_G = 1.2\ I_{GT}$	I - III	Max.	25	50	70	mA
		II		30	60	80	
$dV/dt^{(2)}$	$V_D = 67\ \%V_{DRM}$ gate open	$T_j = 125\text{ }^\circ\text{C}$	Min.	40	500	1000	V/ μs
$(dI/dt)_c^{(2)}$	$(dV/dt)_c = 0.1\text{ V}/\mu\text{s}$	$T_j = 125\text{ }^\circ\text{C}$	Min.	8.5	-	-	A/ms
	$(dV/dt)_c = 10\text{ V}/\mu\text{s}$	$T_j = 125\text{ }^\circ\text{C}$		3.0	-	-	
	Without snubber	$T_j = 125\text{ }^\circ\text{C}$		-	8.5	14	

1. Minimum IGT is guaranteed at 5% of I_{GT} max

**Electrical characteristics ($T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified)
standard (4 quadrants)**

Symbol	Test conditions	Quadrant		Value		Unit
				C	B	
$I_{GT}^{(1)}$	$V_D = 12\text{ V}$ $R_L = 33\ \Omega$	I - II - III IV	Max.	25 50	50 100	mA
V_{GT}		ALL	Max.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_j = 125\text{ }^\circ\text{C}$	ALL	Min.	0.2		V
I_H	$I_T = 500\text{ mA}$		Max.	25	50	mA
I_L	$I_G = 1.2\ I_{GT}$	I - III - IV	Max.	40	60	mA
		II		80	120	
$dV/dt^{(2)}$	$V_D = 67\ \%V_{DRM}$ gate open	$T_j = 125\text{ }^\circ\text{C}$	Min.	200	400	V/ μs
$(dV/dt)_c^{(2)}$	$(dI/dt)_c = 7\text{ A/ms}$	$T_j = 125\text{ }^\circ\text{C}$	Min.	5	10	V/ μs

1. Minimum IGT is guaranteed at 5% of I_{GT} max



Static characteristics

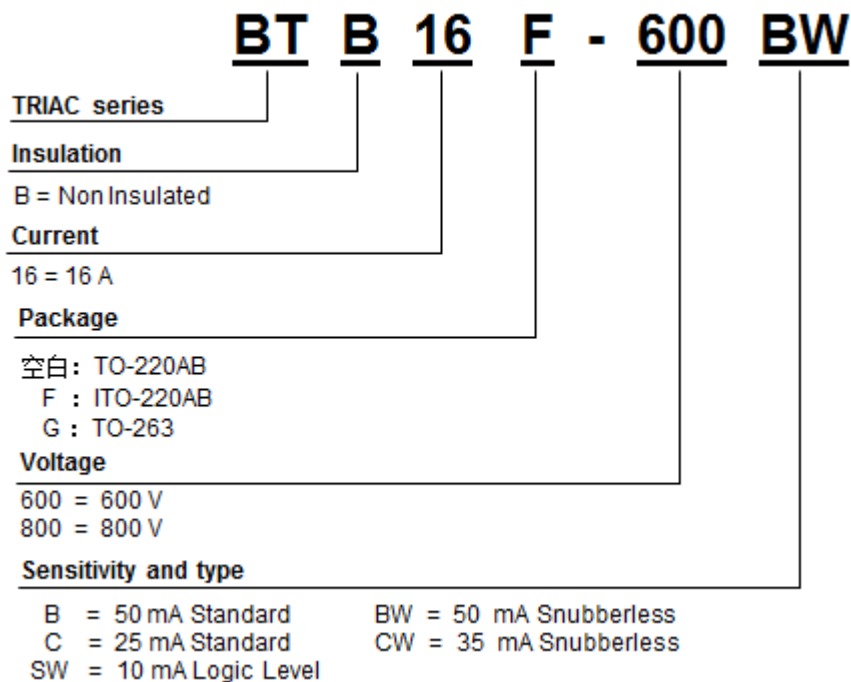
Symbol	Test conditions			Value	Unit	
$V_T(2)$	$I_{TM} = 22.5\text{ A}$	$t_p = 380\ \mu\text{s}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	1.55	V
$V_{to}(2)$	Threshold voltage			Max.	0.85	V
$R_d(2)$	Dynamic resistance			Max.	25	m Ω
I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM}$			Max.	5	μA
					$T_j = 125\text{ }^\circ\text{C}$	2

Thermal resistance

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	D ² PAK / TO-220AB	1.2	$^\circ\text{C/W}$
		ITO-220AB insulated	3.9	
$R_{th(j-a)}$	Junction to ambient	$S^{(1)} = 1\text{ cm}^2$ D ² PAK	45	$^\circ\text{C/W}$
		TO-220AB	60	

1. S = Copper surface under tab

ORDERING INFORMATION





CHARACTERISTICS

Figure 1. Maximum power dissipation versus on-state rms current (full cycle)

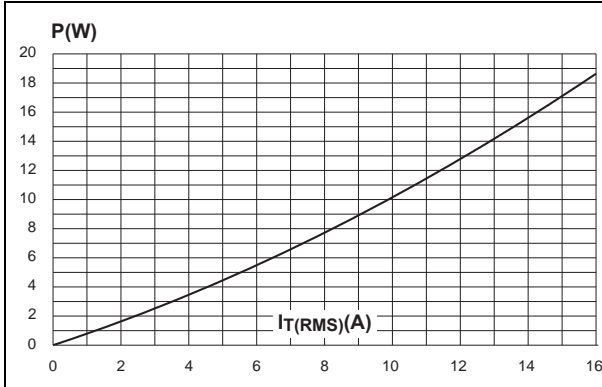


Figure 2. On-state rms current versus case temperature (full cycle)

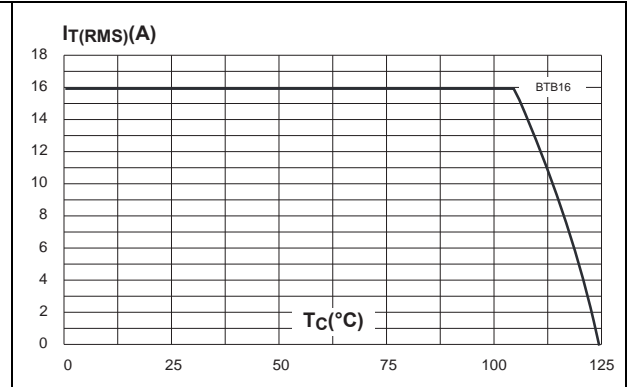


Figure 3. On-state rms current versus ambient temperature (full cycle)

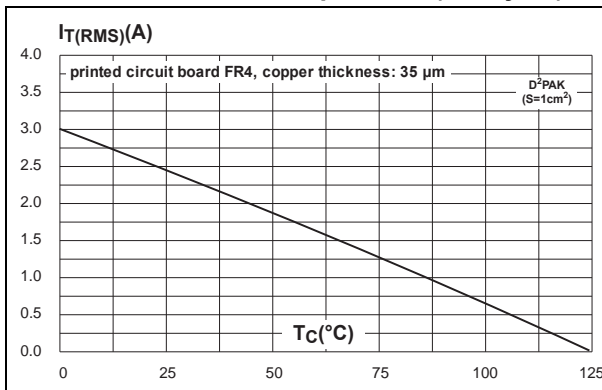


Figure 4. Relative variation of thermal impedance versus pulse duration

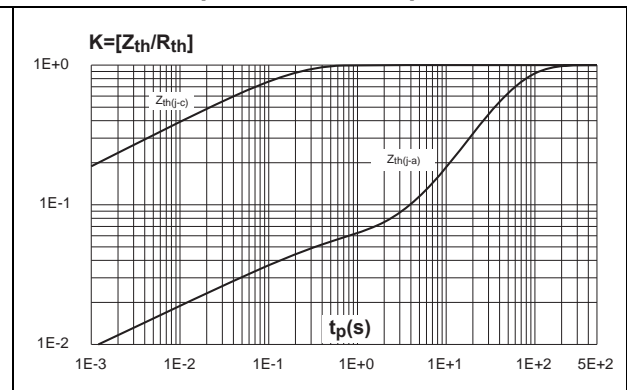


Figure 5. On-state characteristics (maximum values)

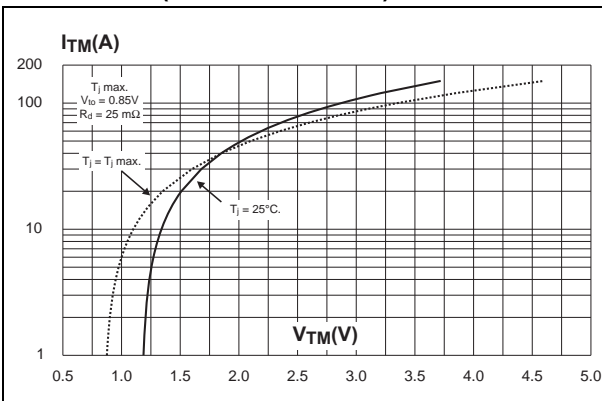
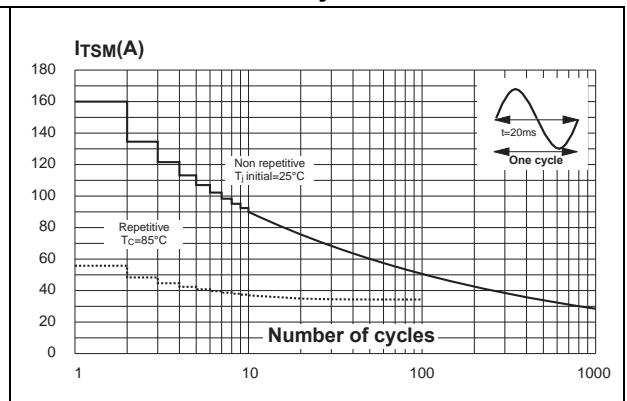


Figure 6. Surge peak on-state current versus number of cycles





CHARACTERISTICS

Figure 7. Non-repetitive surge peak on-state current for a sinusoidal

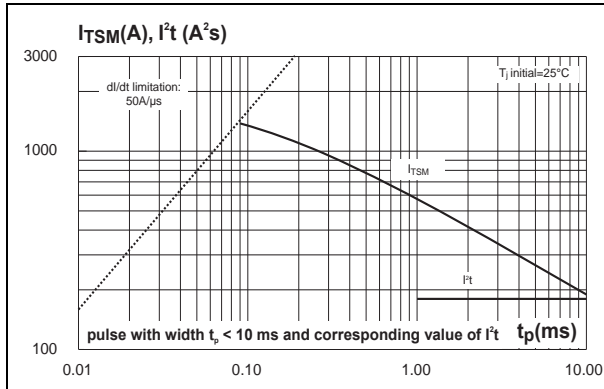


Figure 8. Relative variation of gate trigger current

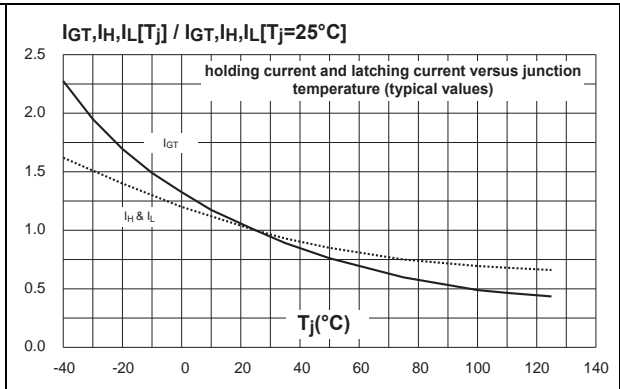


Figure 9. Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values)

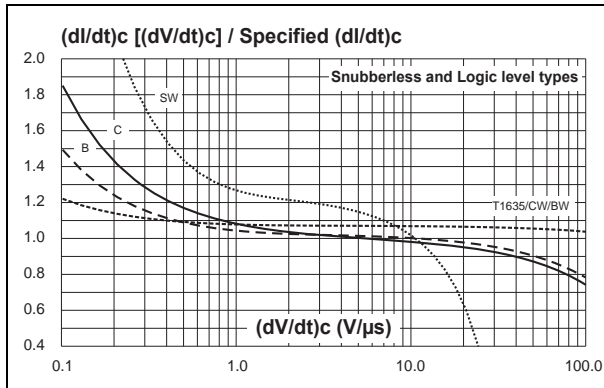


Figure 10. Relative variation of critical rate of decrease of main current versus $(dV/dt)_c$ (typical values)

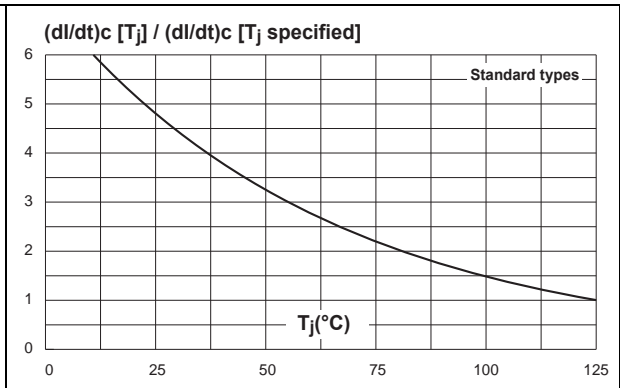
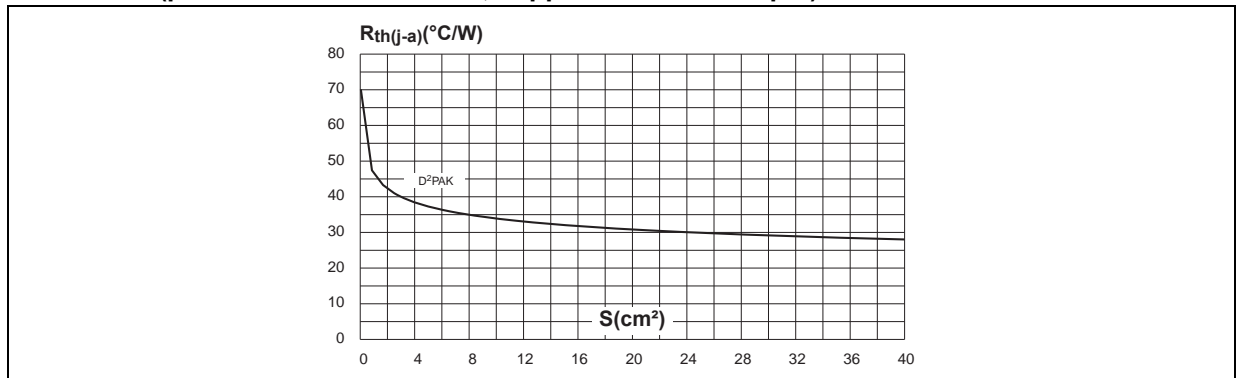
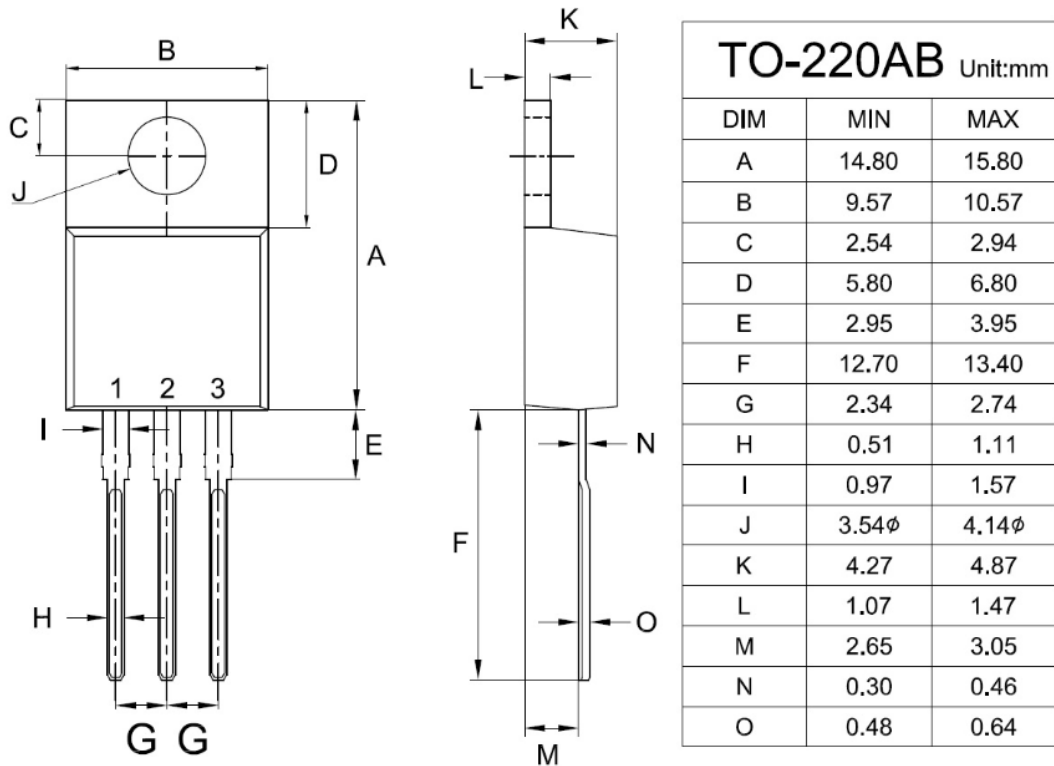


Figure 11. TO-263 thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 μ m)

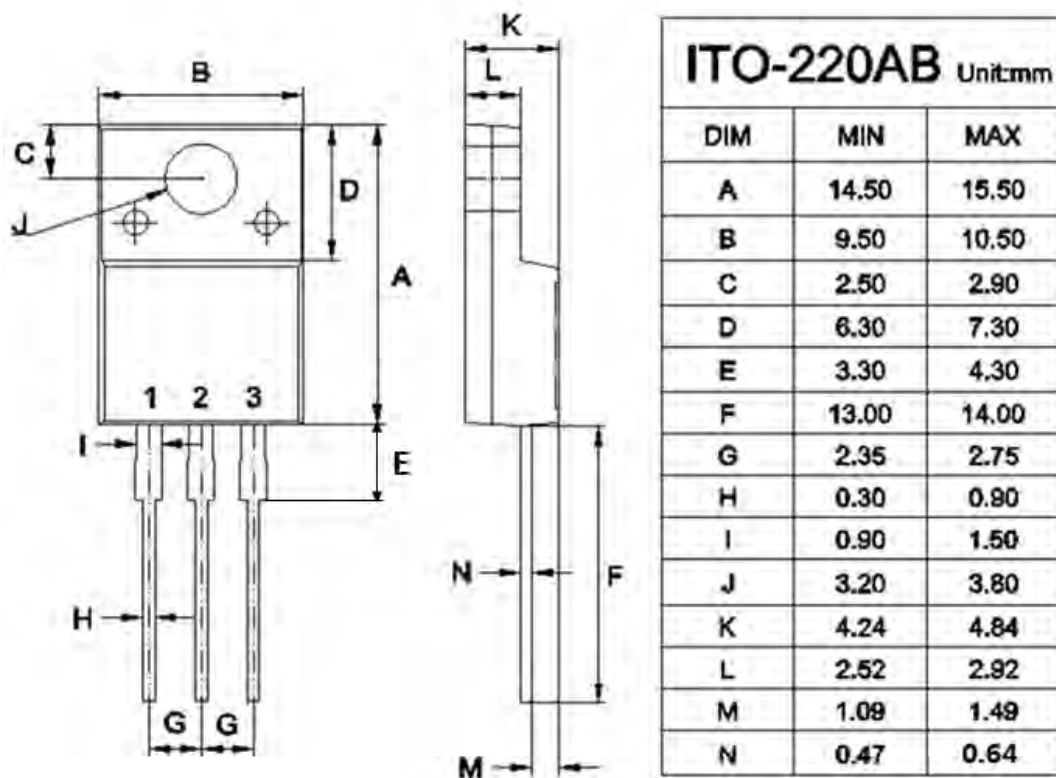




TO-220AB Mechanical Drawing

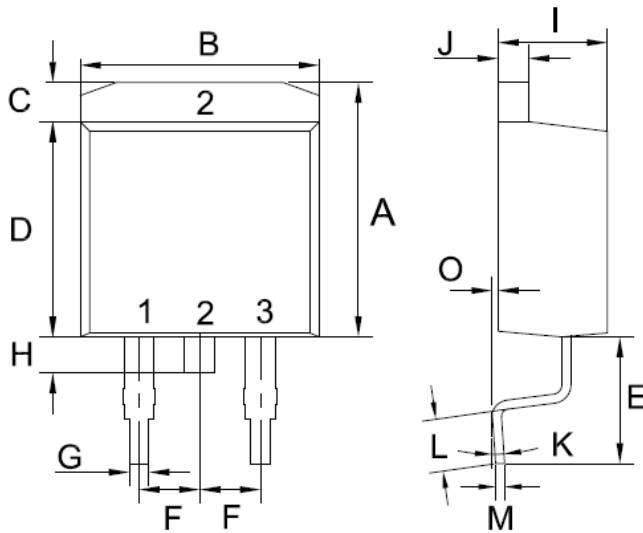


ITO-220AB Mechanical Drawing





TO-263 Mechanical Drawing



TO-263 (D ² PAK)		
Unit:mm		
DIM	MIN	MAX
A	10.44	10.84
B	9.81	10.21
C	1.44	1.84
D	8.80	9.20
E	4.46	4.66
F	2.44	2.64
G	0.61	1.01
H	0.70	1.30
I	4.27	4.87
J	1.07	1.47
K	0°	8°
L	2.10	2.50
M	0.30	0.46
O	0	0.25